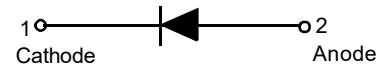
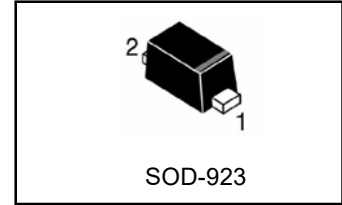


RB751CS-40

S-RB751CS-40

SCHOTTKY BARRIER DIODE



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low current rectification
- Low VF
- High reliability.
- Silicon epitaxial planar

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751CS-40	5	8000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

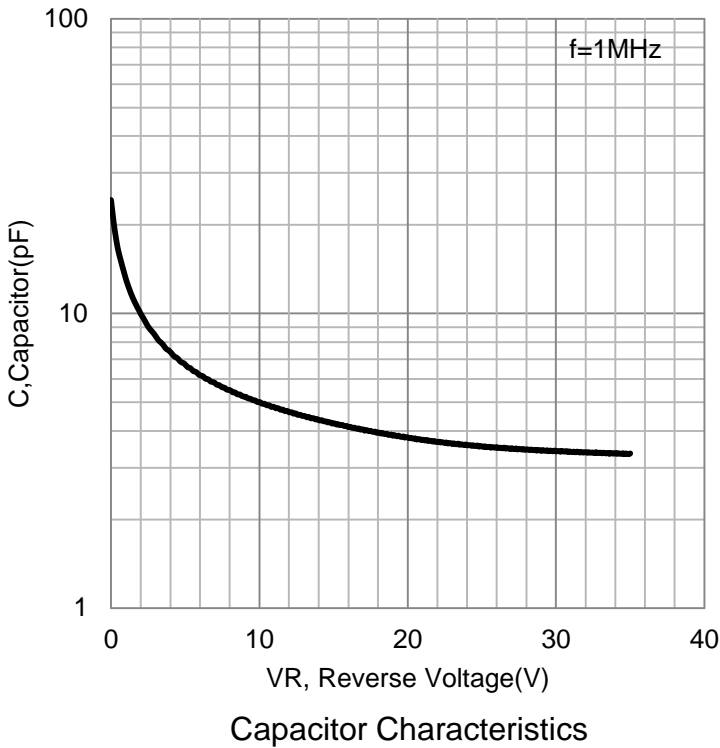
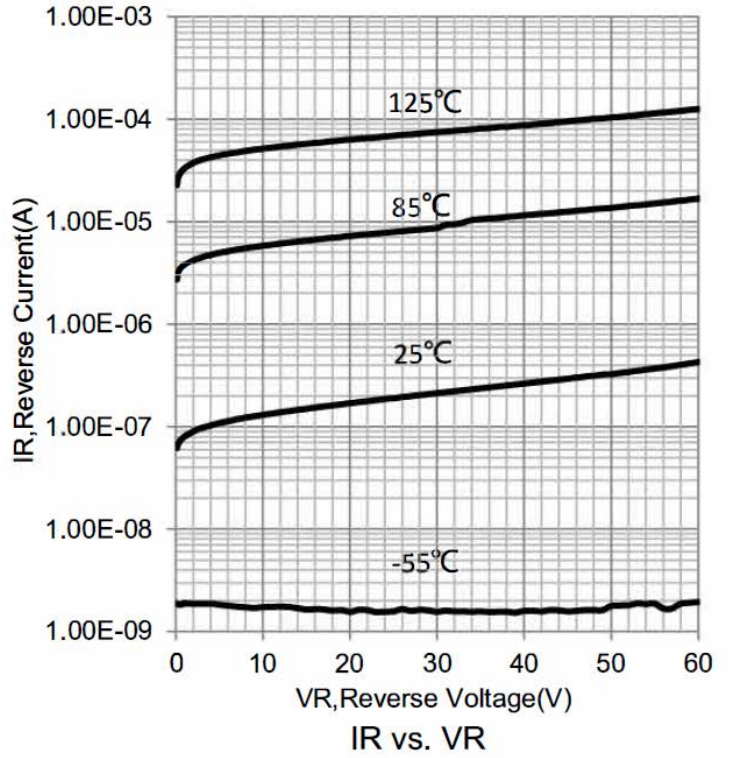
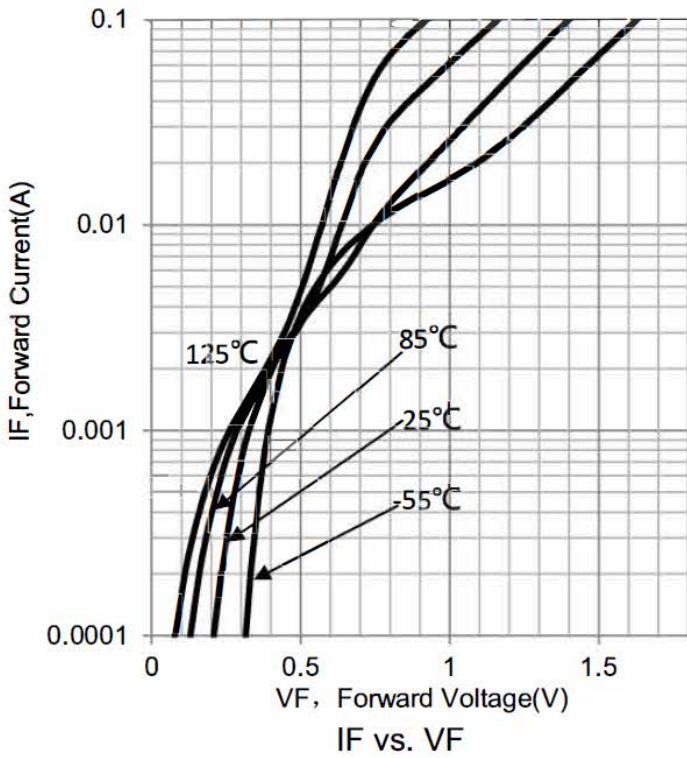
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	40	V
Reverse voltage(DC)	VR	30	V
Average rectified forward current	IO	30	mA
Forward current surge peak (60Hz · 1cyc)	IFSM	200	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40~+125	°C

4. ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	Symbol	Min	Typ	Max	Unit
Forward voltage (IF=1mA)	VF	-	-	0.37	V
Reverse current (VR=30V)	IR	-	-	0.5	μA
Capacitance between terminals (VR =1V , f=1MHz)	Ct	-	1	-	pF



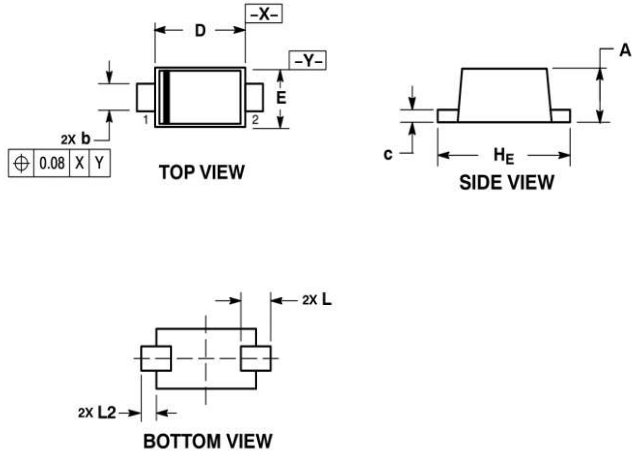
5.ELECTRICAL CHARACTERISTICS CURVES



6. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19REF			0.007REF		
L2	0.05	0.10	0.15	0.002	0.004	0.006

7. SOLDERING FOOTPRINT
